

| L Number | Hits | Search Text                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                | DB                               | Time stamp          |
|----------|------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------|---------------------|
| 8        | 20   | (((((low adj (k or constant or dielectric)) and (inorganic or SiO2 or SiO?sub\$2 or FSG or USG)) and (barrier or SiN or SiC or ((Si or silicon) adj (nitride or carbide)) or Si3N4 or "Si.sub.3 N.sub.4" or "Si.sub.3N.sub.4")) and (dualdamascene or damascene)) or (((low adj (k or constant or dielectric)) and (inorganic or SiO2 or SiO?sub\$2 or FSG or USG)) and (barrier or SiN or SiC or ((Si or silicon) adj (nitride or carbide)) or Si3N4 or "Si.sub.3 N.sub.4" or "Si.sub.3N.sub.4")) and (via or hole or viahole or opening) and (trench or groove)))                                        | EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2004/10/23<br>18:38 |
| 9        | 877  | (((((low adj (k or constant or dielectric)) and (inorganic or SiO2 or SiO?sub\$2 or FSG or USG)) and (barrier or SiN or SiC or ((Si or silicon) adj (nitride or carbide)) or Si3N4 or "Si.sub.3 N.sub.4" or "Si.sub.3N.sub.4")) and (dualdamascene or damascene)) or (((low adj (k or constant or dielectric)) and (inorganic or SiO2 or SiO?sub\$2 or FSG or USG)) and (barrier or SiN or SiC or ((Si or silicon) adj (nitride or carbide)) or Si3N4 or "Si.sub.3 N.sub.4" or "Si.sub.3N.sub.4")) and (via or hole or viahole or opening) and (trench or groove))) and (@ad<=19990630 or @rlad<=19990630) | USPAT;<br>US-PGPUB               | 2004/10/23<br>18:44 |